

14701 Firestone Blvd. \* La Mirada, Ca 90638 Phone: (562) 404-4474 \* Fax: (562) 404-1773 ssdi@ssdi-power.com \* www.ssdi-power.com

## **Designer's Data Sheet**

## Part Number / Ordering Information 1/

SED75\_\_\_ 30 \_\_\_

L Screening<sup>2'</sup> = None
TX = TX Level
TXV = TXV Level
S = S Level
Configuration
KB = without lead

KE = with lead

## **SED75KB30 SED75KE30**

## 75 AMP 30 VOLT SCHOTTKY RECTIFIER

#### **FEATURES:**

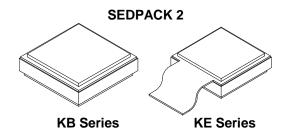
- Low Reverse Leakage
- Low Forward Voltage Drop
- Hermetically Sealed Power Surface Mount Package
- Guard Ring for Overvoltage Protection
- TX, TXV, and Space Level Screening Available<sup>2/2</sup>

MAXIMUM RATINGS	Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, T <sub>A</sub> = 100°C)	Io	75	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, Superimposed on $I_0$ , Allow Junction to Reach Equilibrium between Pulses, $T_A = 25^{\circ}\text{C}$ )	I <sub>FSM</sub>	600	Amps
Operating and Storage Temperature	T <sub>OP</sub> & T <sub>stg</sub>	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R <sub>θJC</sub>	0.7	°C/W

#### Notes:

1/ For Ordering Information, Price, Operating Curves, and Availability – Contact Factory.

2/ Screening to MIL-PRF-19500.





#### Solid State Devices, Inc.

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# **SED75KB30 SED75KE30**

ELECTRICAL CHARACTERISTICS		Symbol	Maximum	Unit
Instantaneous Forward Voltage Drop (T <sub>A</sub> = 25°C, 300 μsec Pulse)	I <sub>F</sub> =50 A <sub>DC</sub> I <sub>F</sub> =75 A <sub>DC</sub>		0.52 0.60	V <sub>DC</sub>
Instantaneous Forward Voltage Drop (I <sub>F</sub> =50 A <sub>DC</sub> , T <sub>A</sub> = +125°C, 300 μsec Pulse)		V <sub>F3</sub>	0.45	V <sub>DC</sub>
Reverse Leakage Current (Rated V <sub>R</sub> , 300 μsec pulse minimum)	$T_A = 25^{\circ}C$ $T_A = 125^{\circ}C$	I <sub>R1</sub> I <sub>R2</sub>	2 450	mA
Junction Capacitance $(V_R = 5 V_{DC}, T_A = 25^{\circ}C, f = 1 MHz)$		<b>C</b> J	4600	pF

